

ABSTRACT

Disclosed is a contact hole forming method for forming gate contact holes and non-gate contact holes. The method of this invention comprises the steps of providing a substrate; forming a plurality of operation layers on the substrate as required, wherein the operation layers of the gate contact hole forming portion comprise at least a gate metal and a cap nitride layer on the gate metal; forming an additional nitride layer on the uppermost layer of the operation layers; forming photoresist on the additional nitride layer to define the positions of the respective contact holes to be formed; forming the non-gate contact hole and removing the portion of the operation layers corresponding to the gate contact hole forming position above the cap nitride by etching; filling the non-gate contact hole with photoresist; and forming the gate contact hole through removing the cap nitride portion corresponding to the gate contact hole forming position and removing all the additional nitride layer by etching.